

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

a wiring including a gate electrode formed over a substrate, the wiring comprising a tungsten nitride film and a tungsten film formed thereon,

wherein the wiring includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the tungsten film is equal to or less than 0.3 ppm.

2. (Previously presented) The device according to claim 1, wherein a thickness of the tungsten nitride film is 10 to 50 nm and a thickness of the tungsten film is 200 to 400 nm.

3. (Previously presented) The device according to claim 1, wherein electrical resistivity of the wiring is equal to or less than 40 $\mu\Omega\cdot\text{cm}$.

4. (Currently Amended) A semiconductor device comprising:

a wiring including a gate electrode formed over a substrate, the wirings comprising a metal film and a nitride film of the metal film,

wherein the metal film is located on the nitride film of the metal film,

wherein the wiring includes at least one inert element and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the metal film is equal to or less than 0.3 ppm.

5. (Previously presented) The device according to claim 4, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

6. (Previously presented) The device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

7. (Previously presented) The device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

8. (Previously presented) The device according to claim 4, wherein the inert element except for the argon is Xe or Kr.

9. (Previously presented) The device according to claim 4, wherein internal stress of the wiring is from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

10. (Previously presented) The device according to claim 4, wherein line width of the wiring is equal to or less than 5μm.

11. (Previously presented) The device according to claim 4, wherein film thickness of the wiring is equal to or greater than 0.1 μm, and equal to or less than 0.7μm.

12. (Previously presented) The device according to claim 4, wherein the wiring is used as a gate electrode of a TFT.

13. (Previously presented) The device according to claim 4, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40Ω .

14. (Previously presented) The device according to claim 4, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

15. (Previously presented) The device according to claim 4, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

16. (Currently Amended) A semiconductor device comprising:
a wiring including a gate electrode formed over a substrate, the wiring comprising a tungsten nitride film and a tungsten film formed thereon; and
an insulating film formed over the wiring, said insulating film comprising SiOxNy ,
wherein the wiring includes at least one inert element and 90% or more of the inert element is argon, and
wherein an amount of sodium contained within the tungsten film is equal to or less than 0.3

ppm.

17. (Previously presented) The device according to claim 16, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

18. (Previously presented) The device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

19. (Previously presented) The device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

20. (Previously presented) The device according to claim 16, wherein the inert element except for argon is Xe or Kr.

21. (Previously presented) The device according to claim 16, wherein internal stress of the wiring is from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

22. (Previously presented) The device according to claim 16, wherein line width of the wiring is equal to or less than 5 μ m.

23. (Previously presented) The device according to claim 16, wherein film thickness of the wiring is equal to or greater than 0.1 μ m, and equal to or less than 0.7 μ m.

24. (Previously presented) The device according to claim 16, wherein the wiring is used as a gate electrode of a TFT.

25. (Previously presented) The device according to claim 16, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40Ω .

26. (Previously presented) The device according to claim 16, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

27. (Previously presented) The device according to claim 16, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

28. (Previously Presented) A semiconductor device comprising:
a wiring formed over a substrate having a lamination structure comprising a phosphorus doped silicon, a nitride film of tungsten, and a film comprising tungsten,
wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and
wherein an amount of sodium contained within the film comprising tungsten is equal to or less than 0.3 ppm.

29. (Previously presented) The device according to claim 28, wherein the wiring is further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

30. (Previously presented) The device according to claim 28, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

31. (Previously presented) The device according to claim 28, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

32. (Previously presented) The device according to claim 28, wherein the inert element except for argon is Xe or Kr.

33. (Previously presented) The device according to claim 28, wherein internal stress of the wiring is from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

34. (Previously presented) The device according to claim 28, wherein line width of the wiring is equal to or less than 5 μ m.

35. (Previously presented) The device according to claim 28, wherein film thickness of the wiring is equal to or greater than 0.1 μ m, and equal to or less than 0.7 μ m.

36. (Previously presented) The device according to claim 28, wherein the wiring is used as a gate electrode of a TFT.

37. (Previously presented) The device according to claim 28, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 Ω .

38. (Previously presented) The device according to claim 28, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

39. (Previously presented) The device according to claim 28, wherein the semiconductor device is an at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

40. (Currently Amended) A semiconductor device comprising:
a wiring including a gate electrode formed over a substrate, the wiring having a lamination structure containing a tungsten nitride film and a film comprising tungsten formed thereon,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the film comprising tungsten is equal to or less than 0.3 ppm.

41. (Previously presented) The device according to claim 40, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

42. (Previously presented) The device according to claim 40, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

43. (Previously presented) The device according to claim 40, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

44. (Previously presented) The device according to claim 40, wherein the inert element except for argon is Xe or Kr.

45. (Previously presented) The device according to claim 40, wherein internal stress of the wiring is from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

46. (Previously presented) The device according to claim 40, wherein line width of the wiring is equal to or less than 5 μ m.

47. (Previously presented) The device according to claim 40, wherein film thickness of the wiring is equal to or greater than 0.1 μ m, and equal to or less than 0.7 μ m.

48. (Previously presented) The device according to claim 40, wherein the wiring is used as a

gate electrode of a TFT.

49. (Previously presented) The device according to claim 40, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 Ω .

50. (Previously presented) The device according to claim 40, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

51. (Previously presented) The device according to claim 40, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

52. (Currently Amended) A semiconductor device comprising:
a wiring including a gate electrode formed over a substrate, the wiring comprising a tungsten nitride film and a film comprising tungsten formed thereon,
wherein the wiring includes at least one inert element, and 90% or more of the inert element is argon,
wherein an amount of sodium contained within the film comprising tungsten is equal to or less than 0.3 ppm, and
wherein internal stress of the wiring is from $-1 \times 10^{10} \text{ dyn/cm}^2$ to $+1 \times 10^{10} \text{ dyn/cm}^2$.

53-63 (Canceled).